

HSU119

Silicon Epitaxial Planar Diode for High Speed Switching

REJ03G0190-0100Z

(Previous: ADE-208-444)

Rev.1.00

Mar.22.2004

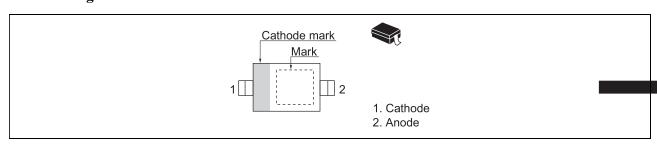
Features

- Low capacitance. (C = 2.0 pF max)
- Short reverse recovery time. $(t_{rr} = 3.0 \text{ ns max})$
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSU119	H1	URP

Pin Arrangement



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit	
Peak reverse voltage	V_{RM}	85	V	
Reverse voltage	V _R	80	V	
Peak forward current	I _{FM}	300	mA	
Non-Repetitive peak forward surge current	I _{FSM} * ¹	4	Α	
Average rectified current	Io	100	mA	
Junction temperature	Tj	125	°C	
Storage temperature	Tstg	-55 to +125	°C	

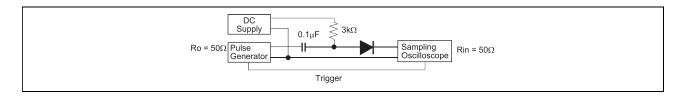
Note: 1. Within 1µs forward surge current.

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V_{F1}	_	_	8.0	V	I _F = 10 mA
	V _{F2}	_	_	1.2		I _F = 100 mA
Reverse current	I _R	_	_	0.1	μΑ	V _R = 80 V
Capacitance	С	_	_	2.0	pF	V _R = 0 V, f = 1 MHz
Reverse recovery time*1	t _{rr}	_	_	3.0	ns	I_F = 10 mA, V_R = 6 V, R_L = 50 Ω

Note: 1. Reverse recovery time test circuit



Main Characteristics

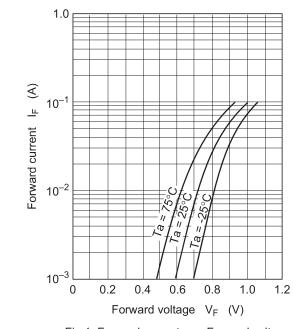


Fig.1 Forward current vs. Forward voltage

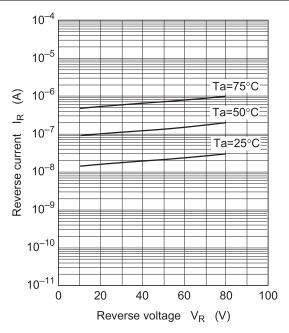
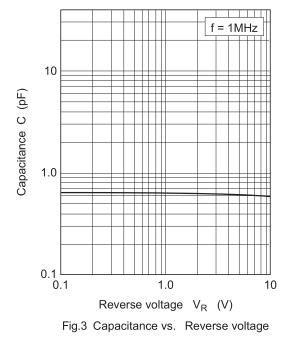
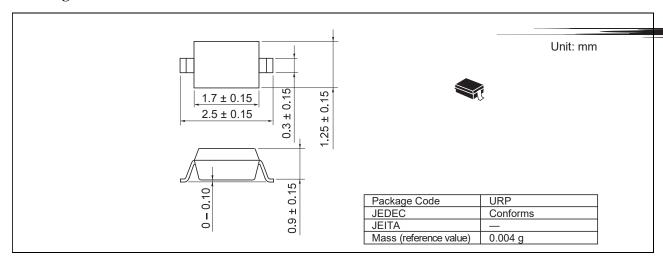


Fig.2 Reverse current vs. Reverse voltage



Package Dimensions



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